



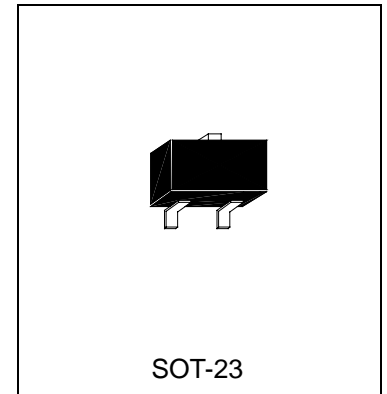
HBAT54\A\C\S

Description

Silicon Schottky Barrier Double Diodes

Features

These diodes feature very low turn-on voltage and fast switching. There is a PN junction guard ring against excessive voltage such as electronics attic discharges protects these devices.



Absolute Maximum Ratings

- Maximum Temperatures
 - Storage Temperature -65~+125 °C
 - Junction Temperature +125 °C
- Maximum Power Dissipation
 - Total Power Dissipation (Ta=25°C) 230 mW
- Maximum Voltages and Currents (Ta=25°C)
 - Repetitive Peak Reverse Voltage 30 V
 - Forward Continuous Current 200 mA
 - Repetitive Peak Forward Current 300 mA
 - Surge Forward Current (tp<1s)..... 600 mA

Characteristics (Ta=25°C)

Characteristic	Symbol	Condition	Min.	Max.	Unit
Reverse breakdown Voltage	V(BR)R	IR=10uA	30	-	V
Forward Voltage	VF(1)	IF=0.1mA	-	240	mV
	VF(2)	IF=1mA	-	320	mV
	VF(3)	IF=10mA	-	400	mV
	VF(4)	IF=30mA	-	500	mV
	VF(5)	IF=100mA	-	1000	mV
Reverse Current	IR	VR=25V	-	2.0	uA
Total Capacitance	CT	VR=1V, f=1MHz	-	10	pF
Reverse Recovery Time	Trr	IF=IR=10mA RL=100Ω measured at IR=1mA	-	5	nS



Characteristics Curve

